

isc Silicon NPN Power Transistor

BUW12

DESCRIPTION

- Collector-Emitter Sustaining Voltage-: V_{CEO(SUS)}= 400V(Min.)
- Low Collector Saturation Voltage-
- : V_{CE(sat)}= 1.5V(Max.)@I_C= 6A
- High Speed Switching
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

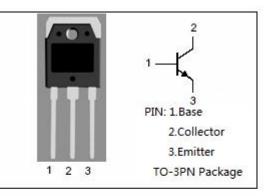
APPLICATIONS

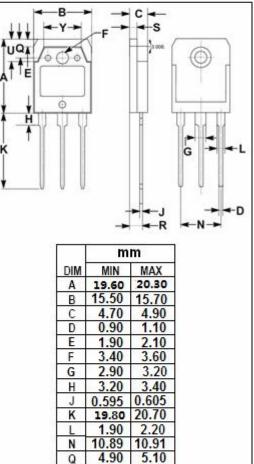
Designed for high voltage, fast switching industrial applications.

SYMBOL	IBOL PARAMETER		UNIT	
V _{CBO}	Collector-Base Voltage 850		V	
VCEO	Collector-Emitter Voltage	tter Voltage 400		
V _{EBO}	Emitter-Base Voltage	9	V	
lc	Collector Current-Continuous	r Current-Peak 20		
I _{CM}	Collector Current-Peak			
I _B	Base Current			
I _{BM}	Base Current-Peak	6	А	
Pc	Collector Power Dissipation $@T_c=25^{\circ}C$	125	W	
Tj	Junction Temperature	unction Temperature 150		
T _{stg}	Storage Temperature Range -65~150		°C	

THERMAL CHARACTERISTICS

SYMBOL	SYMBOL PARAMETER Rth j-c Thermal Resistance, Junction to Case		UNIT
R _{th j-c}			°C/W





1

R

S

U Y 3.35

5.90

9.90

1.995

3.45

2.100

6.20

10.10

isc website: <u>www.iscsemi.com</u>



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ELECTRICAL CHARACTERISTICS

$T_{\text{C}}\text{=}25^{\circ}\!\!\!^{\circ}\!\!^{\circ}_{\operatorname{C}}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	МАХ	UNIT
V _{CEO(SUS)}	Collector-Emitter Sustaining Voltage	I _C =50mA; I _B = 0	400			V
V _{CE(sat)}	Collector-Emitter Saturation Voltage	I _C = 6A; I _B = 1.2A			1.5	V
V _{BE(sat)}	Base-Emitter Saturation Voltage	I _C = 6A; I _B = 1.2A			1.5	V
I _{CES}	Collector Cutoff Current	V _{CE} =V _{CES} ;V _{BE} = 0 V _{CE} =V _{CES} ;V _{BE} = 0;T _C =125°C			1.0 3.0	mA
I _{EBO}	Emitter Cutoff Current	V _{EB} = 9V; I _C = 0			10	mA
h _{FE-1}	DC Current Gain	Ic= 10mA; Vce= 5V	10		35	
h _{FE-2}	DC Current Gain	I _C = 1A; V _{CE} = 5V	10		35	

Switching Times; Resistive Load

ton	Turn-on Time	I _C = 6A;I _{B1} = -I _{B2} = 1.2A		1.0	μs
ts	Storage Time			4.0	μs
tr	Fall Time			0.8	μ S

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